



DMG4N65CT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) MAX}	Package	$I_{D MAX}$ $T_{C} = +25^{\circ}C$
650V	$3.0\Omega@V_{GS} = 10V$	TO220-3	4.0A

Description

This new generation complementary MOSFET features low onresistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

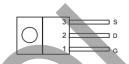
Mechanical Data

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

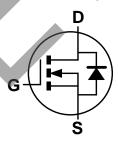
TO220-3



Top View



Top View Pin Out Configuration



Equivalent Circuit

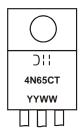
Ordering Information (Note 4)

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Part Number		Case	Packaging
DMG4N65CT		TO220-3	50 pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¹¹= Manufacturer's Marking
 4N65CT = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 19 = 2019)
 WW = Week (01 to 53)

DMG4N65CT
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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Charac	cteristic		Symbol	Value	Unit	
Drain-Source Voltage			V_{DSS}	650	V	
Gate-Source Voltage			V _{GSS}	±30	V	
Continuous Drain Current (Note 5)	Steady	T _C = +25°C		4.0	^	
V _{GS} = 10V Sta	State	T _C = +70°C	ID	3.0	A	
Pulsed Drain Current (Note 7)			I _{DM}	6	Α	
Avalanche Current (Note 8) V _{DD} = 10	00V, V _{GS} = 10V, I	_ = 60mH	I _{AS}	3.9	А	
Repetitive avalanche energy (Note 7	()		E _{AS}	456	mJ	

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_{D}	2.19	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	RθJA	58.5	°C/W
Power Dissipation (Note 6)	P _D	9.14	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	Reja	2.85	°C/W
Thermal Resistance, Junction to Case @T _A = +25°C (Note 6)	Rejc	0.86	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

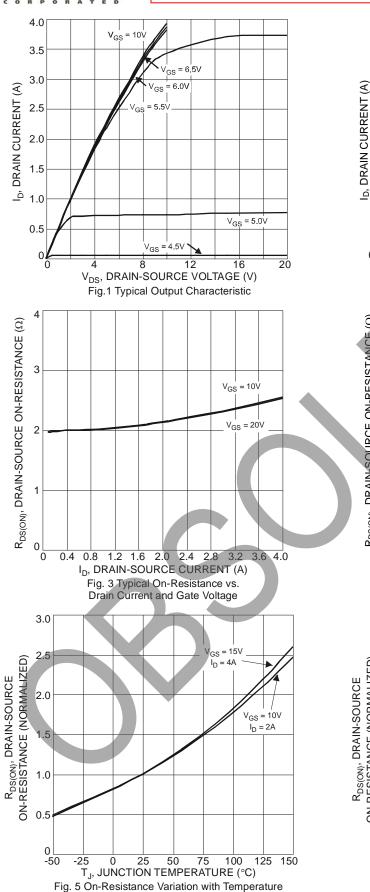
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	650		_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		—	1.0	μΑ	$V_{DS} = 650V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}		_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	3	_	5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	2.1	3.0	Ω	$V_{GS} = 10V, I_D = 2A$
Forward Transfer Admittance	Y _{fs}	_	3.7		s	$V_{DS} = 40V, I_{D} = 2A$
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	_	900	_		V 05V V 0V
Output Capacitance	Coss	_	50		$V_{DS} = 25V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	1.1			1 – 1.01011 12
Gate Resistance	R_g	_	2.4		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	13.5	_		10)/)/ 500)/
Gate-Source Charge	Q _{gs}	_	2.7	_	nC	$V_{GS} = 10V, V_{DS} = 520V,$
Gate-Drain Charge	Q_{gd}	_	3.8	_		$I_D = 4A$
Turn-On Delay Time	t _{D(ON)}	_	15.1	_	ns	
Turn-On Rise Time	t _R	_	13.8	_	ns	$V_{GS} = 10V, V_{DS} = 325V,$
Turn-Off Delay Time	t _{D(OFF)}	_	40	_	ns	$R_g = 25\Omega$, $I_D = 4A$
Turn-Off Fall Time	t _F	_	16		ns	
Body Diode Reverse Recovery Time	t _{RR}	_	515	_	ns	$dI/dt = 100A/\mu s$, $V_{DS} = 100V$,
Body Diode Reverse Recovery Charge	Q_{RR}	_	2330	_	nC	$I_F = 4A$

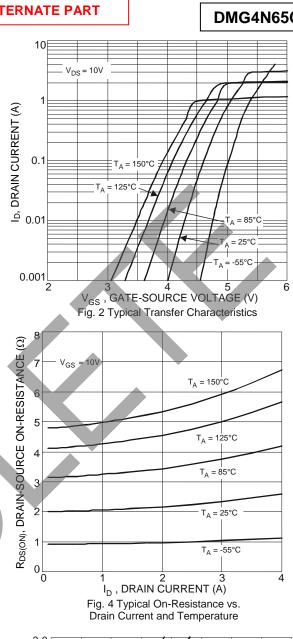
Notes:

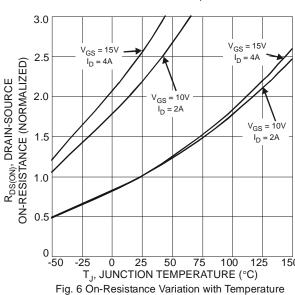
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 6. Device mounted on an infinite heatsink
- 7. Repetitive rating, pulse width limited by junction temperature.
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to production testing.



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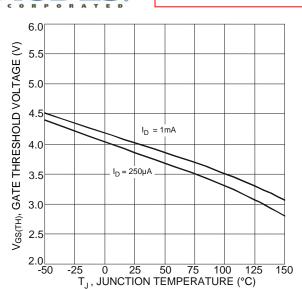


Fig. 7 Gate Threshold Variation vs. Junction Temperature

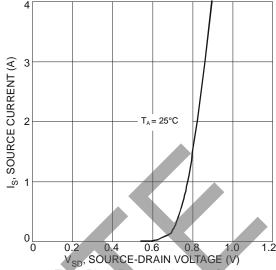


Fig.8 Diode Forward Voltage vs. Current

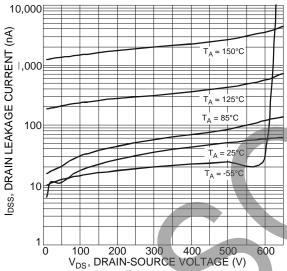
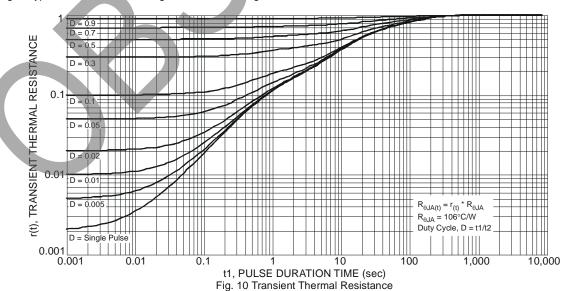


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

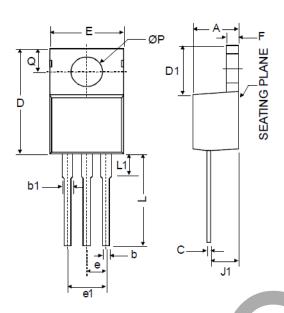




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220-3



TO220-3					
Dim	Dim Min				
Α	3.55	4.85			
b	0.51	1.14			
b1	1,14	1.78			
C	0.31	1.14			
D	14.20	16.50			
D1	5.84	6.86			
E	9.70	10.70			
е	2.79	2.99			
e1	4.83	5.33			
F	0.51	1.40			
J1	2.03	2.92			
L	12.72	14.72			
L1	3.66	6.35			
Р	3.53	4.09			
Q	2.54	3.43			
All Dimensions in mm					



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